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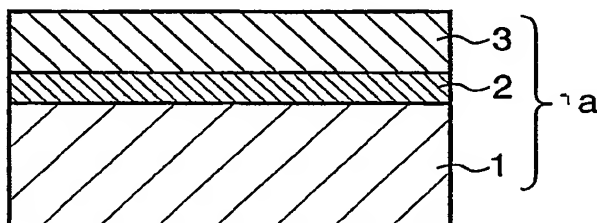
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- (71) Applicant (for all designated States except US): CANON KABUSHIKI KAISHA [JP/JP]; 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 146-8501 (JP).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): SEKIGUCHI, Yoshinobu [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 146-8501 (JP). YONEHARA, Takao [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 146-8501 (JP). KOTO, Makoto [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 146-8501 (JP). OKUDA, Masahiro [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 146-8501 (JP). SHIMADA, Tetsuya [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 146-8501 (JP).
- (74) Agent: OHTSUKA, Yasunori; 7th FL., Shuwa Kioicho Park Bldg., 3-6, Kioicho, Chiyoda-ku, Tokyo 102-0094 (JP).
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(54) Title: SEMICONDUCTOR FILM MANUFACTURING METHOD AND SUBSTRATE MANUFACTURING METHOD



(57) Abstract: This invention provides a semiconductor film manufacturing method using a new separation technique and applications thereof. The semiconductor film manufacturing method of this invention includes a separation layer forming step of hetero-epitaxially growing a separation layer (2) on a seed substrate (1), a semiconductor film forming step of forming a semiconductor film (3) on the separation layer (2), and a separation step of separating, by using the separation layer (2), the semiconductor film (3) from a composite member (1a) formed in the semiconductor film forming step.

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